

N-channel TrenchMOS intermediate level FET

Rev. 2 — 14 October 2010

Product data sheet

1. Product profile

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for intermediate level gate drive sources

1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control

1.4 Quick reference data

Table 1. Quick reference data

- Suitable for thermally demanding environments due to 175 °C rating
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	-	100	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	204	W
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 11</u>		-	2.4	2.8	mΩ



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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Avalanche	e ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 100 \text{ A}; \text{V}_{\text{sup}} \leq 30 \text{ V}; \\ R_{\text{GS}} &= 50 \Omega; \text{V}_{\text{GS}} = 10 \text{ V}; \\ T_{j(\text{init})} &= 25 ^{\circ}\text{C}; \text{ unclamped} \end{split} $	-	-	501	mJ
Dynamic of	characteristics					
Q _{GD}	gate-drain charge	$\begin{split} I_D &= 25 \text{ A}; V_{DS} = 24 $	-	33.3	-	nC

[1] Continuous current is limited by package.

Pinning information 2.

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

Ordering information 3.

Table 3. Ordering	information		
Type number	Package		
	Name	Description	Version
BUK662R5-30C	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	30	V
V _{GS}	gate-source voltage	DC	<u>[1]</u>	-16	16	V
		Pulsed	[2]	-20	20	V
ID	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$	[3]	-	100	А
		T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 1	<u>[3]</u>	-	100	А
I _{DM}	peak drain current	$T_{mb} = 25 \text{ °C}; t_p \le 10 \mu\text{s}; \text{ pulsed};$ see Figure 3		-	783	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	204	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
I _S	source current	T _{mb} = 25 °C	[3]	-	100	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	783	А
Avalanche r	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ld} \begin{array}{l} I_{D} = 100 \; A; \; V_{sup} \leq 30 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped \end{array}$		-	501	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy		[4][5][6]	-	-	J

[1] -16V accumulated duration not to exceed 168 hrs.

[2] Accumulated pulse duration not to exceed 5 mins.

[3] Continuous current is limited by package.

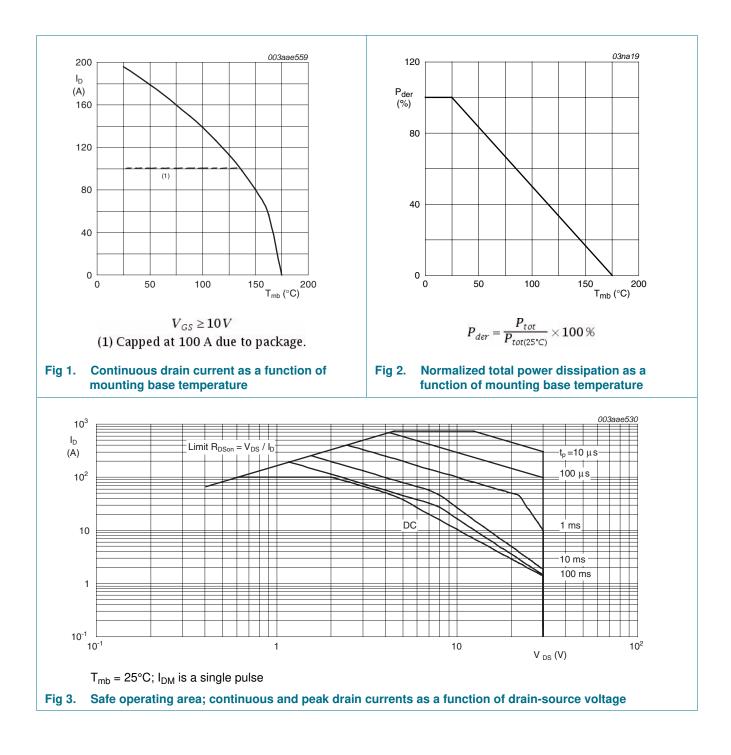
[4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[5] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[6] Refer to application note AN10273 for further information.

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5. Thermal characteristics

mbol	Parameter	Conditions	Min Typ	Max	Unit
(j-mb)	thermal resistance from junction to mounting base	see <u>Figure 4</u>		0.74	K/W
1				003aae531	
Z _{th(j-mb)} (K/W)	δ = 0.5				
10 ⁻¹	0.1				
10 ⁻²	0.02		P	$\delta = \frac{t_p}{T}$	
	single shot				
10 ⁻³)-6 10 ⁻⁵	10 ⁻⁴ 10 ⁻³ 10 ⁻²		▶ · · · ·	
10	10 5	10 - 10 -	10 ⁻¹ tp	(s) I	

Table 5. Thermal characteristi

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6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$	30	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	3.3	V
		I_D = 2.5 mA; V_{DS} = V_{GS} ; T_j = 175 °C; see <u>Figure 10</u>	0.8	-	-	V
IDSS	drain leakage current	$V_{DS}=30~V;~V_{GS}=0~V;~T_{j}=25~^{\circ}C$	-	0.02	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	V
I _{GSS}	gate leakage current	$V_{DS} = 0 V; V_{GS} = 20 V; T_j = 25 \ ^{\circ}C$	-	2	100	nA
		$V_{DS} = 0 V; V_{GS} = -20 V; T_j = 25 \ ^{\circ}C$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u>	-	2.4	2.8	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u>	-	3.6	4.8	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u>	-	3.1	3.9	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>	-	-	5.3	mΩ
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>	-	114	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 5 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>	-	66	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$	-	18	-	nC
Q _{GD}	gate-drain charge	see <u>Figure 13;</u> see <u>Figure 14</u>	-	33.3	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	5216	6960	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 15}{\text{Figure } 15}$	-	896	1100	pF
C _{rss}	reverse transfer capacitance		-	537	740	pF
d(on)	turn-on delay time	$V_{DS} = 25 \text{ V}; \text{ R}_{L} = 1 \ \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	22	-	ns
r	rise time	$R_{G(ext)} = 10 \ \Omega$	-	59	-	ns
d(off)	turn-off delay time		-	209	-	ns
t _f	fall time		-	113	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$	-	3.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; $T_i = 25 \text{ °C}$	-	7.5	-	nH

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003aae780

4.0

3.8

 $V_{GS}(V) = 4.5$

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Table 6.	Characteristics continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 16</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 20 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V};$	-	50	-	ns
Qr	recovered charge	$V_{DS} = 25 V$	-	73	-	nC

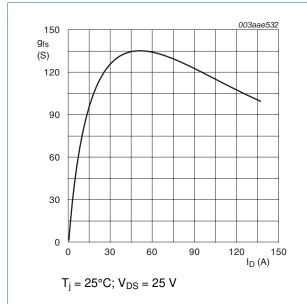
240

180

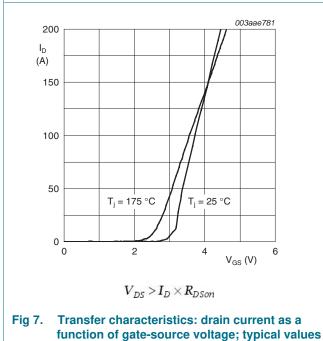
120

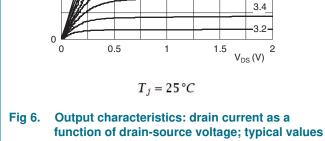
60

I_D (A)





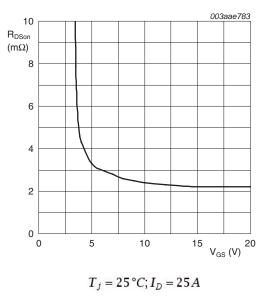




5.0

10.0

6.0

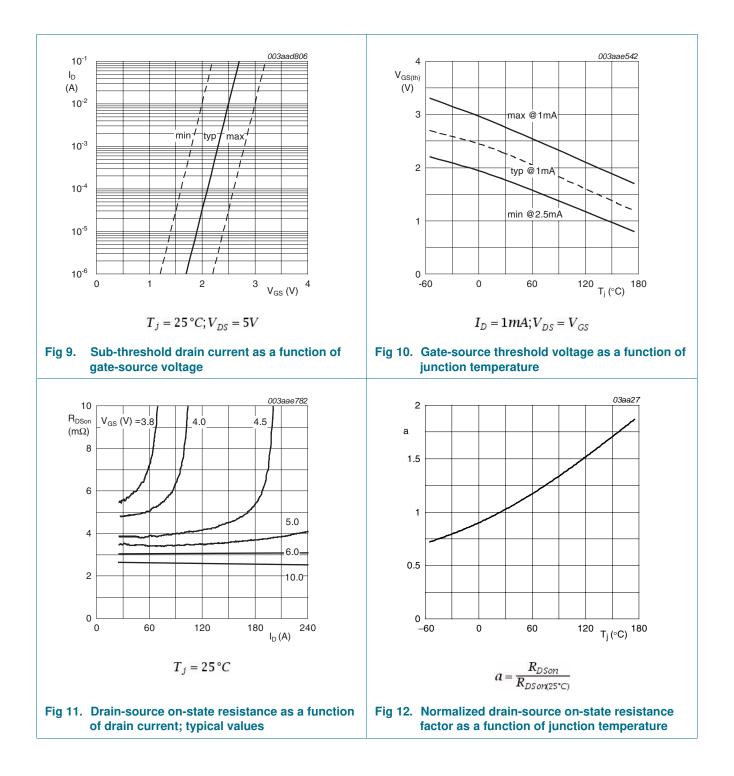




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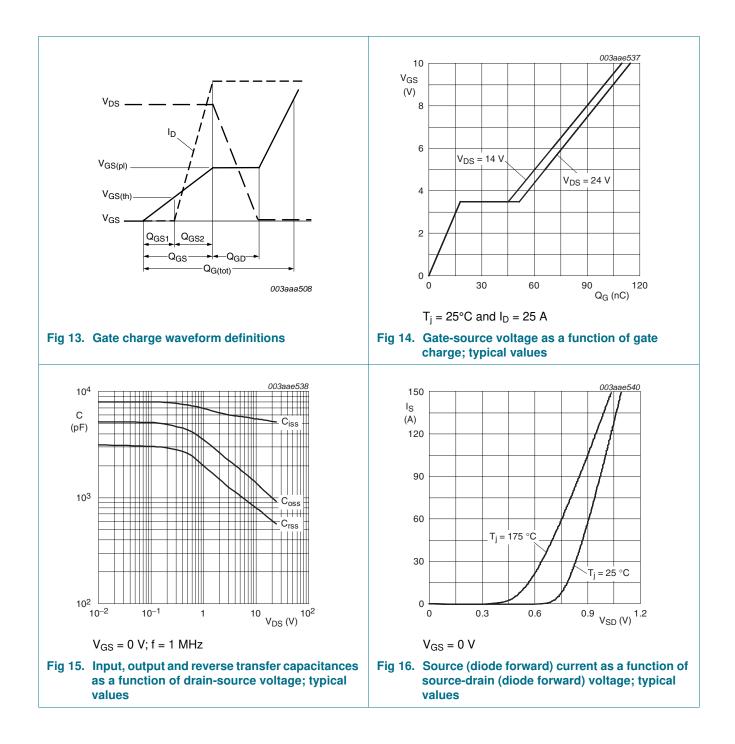
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7. Package outline

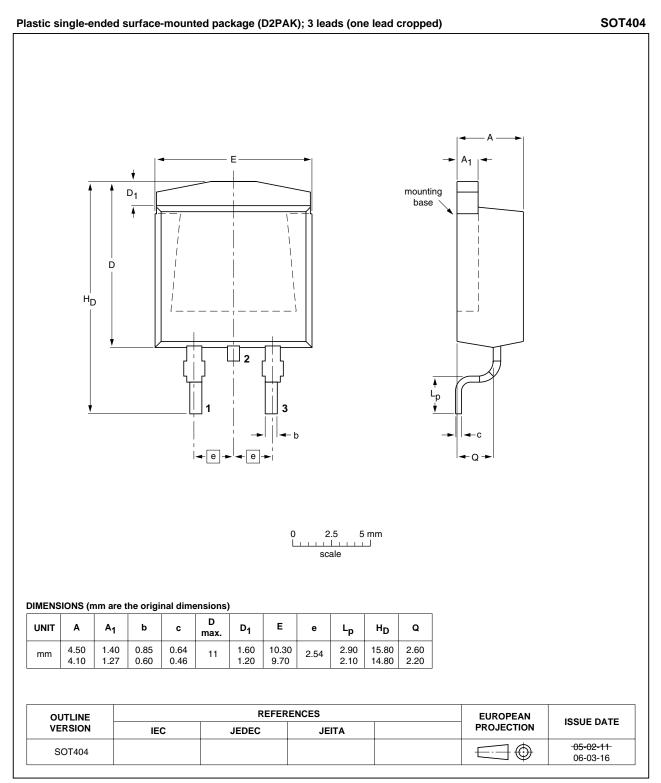


Fig 17. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. **Revision history Document ID Release date** Data sheet status **Change notice** Supersedes BUK662R5-30C v.2 20101014 Product data sheet BUK662R5-30C v.1 -Modifications: • Status changed from objective to product. BUK662R5-30C v.1 20100923 Objective data sheet --

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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